

Product Overview

MBRS2H100T3G: Schottky Power Rectifier, Surface Mount, 2.0 A, 100 V

For complete documentation, see the data sheet.

The Schottky Rectifier employs the Schottky Barrier principle in a metal-to-silicon power rectifier. It features epitaxial construction with oxide passivation and metal overlay contact. It is ideally suited for low voltage, high frequency switching power supplies, free wheeling diodes and polarity protection diodes.

Features

- Compact Package with J-Bend Leads Ideal for Automated Handling
- Highly Stable Oxide Passivated Junction
- Guard-Ring for Overvoltage Protection
- Low Forward Voltage Drop
- This is a Pb-Free Device Mechanical Characteristics:
- Case: Molded Epoxy
- Epoxy Meets UL 94 V-0 @ 0.125 in
- Weight: 70 mg (approximately)
- Cathode Polarity Band
- Lead and Mounting Surface Temperature for Soldering Purposes: 260C Max. for 10 Seconds

For more features, see the data sheet

Benefits

- Low Power Loss / High Efficiency

Applications

- Power Supplies
- Free Wheeling Diodes
- Polarity Protection Diodes

End Products

- LED Lamps

Part Electrical Specifications

Product	Pricing (\$/Unit)	Compliance	Status	Configuration	V_{RRM} Min (V)	V_F Max (V)	I_{RM} Max (μ A)	$I_{O(rec)}$ Max (A)	I_{FSM} Max (A)	t_r Max (ns)	C_j Max (pF)	Package Type
MBRS2H100T3G	0.1491	Pb-free	Active	Single	100	0.79	8	2	130	-	-	SMB-2
		Halide free non AEC-Q and PPAP										
NBRS2H100T3G	0.2328	AEC Qualified PPAP Capable Pb-free Halide free	Active	Single	100	0.79	8	2	130	-	-	SMB-2
NBRS2H100T3G-VF01	0.1863	AEC Qualified	Active	Single	100	0.79	8	2	130	-	-	SMB-2
		PPAP Capable Pb-free Halide free										

For more information please contact your local sales support at www.onsemi.com.

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